

/ Descriptions

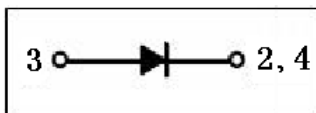
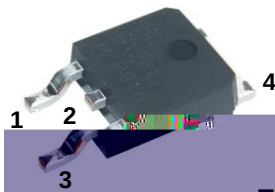
Ultrafast Recovery Diode in a TO-252 Plastic Package.

/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

/ Applications

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit**/ Pinning**

PIN1 NC

PIN 2 Cathode

PIN 3 Anode

PIN 4:Case

/ h_{FE} Classifications & Marking

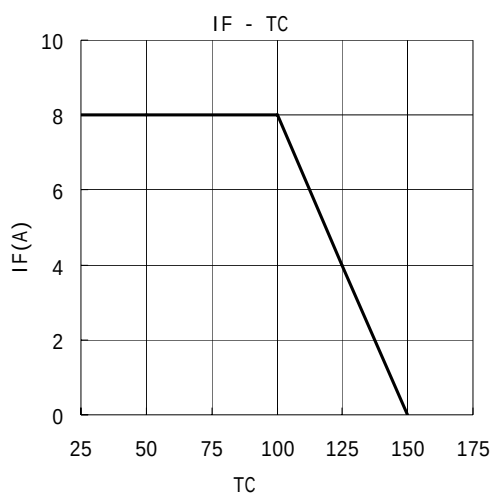
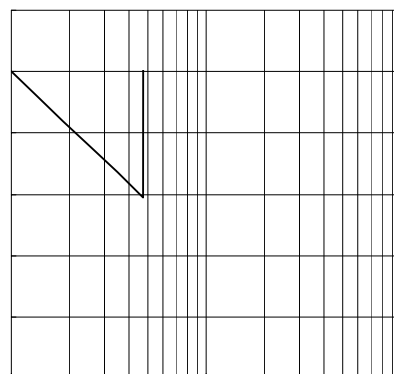
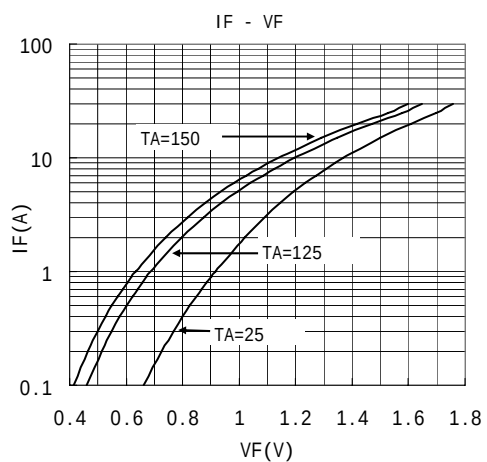
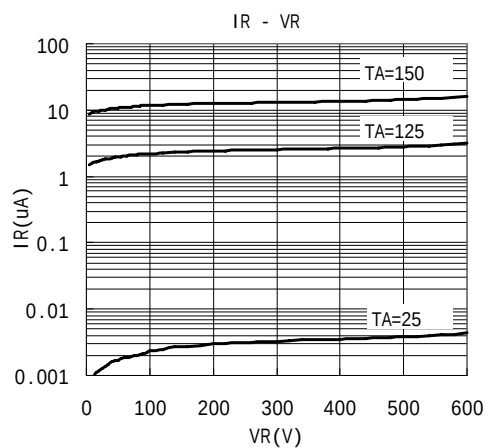
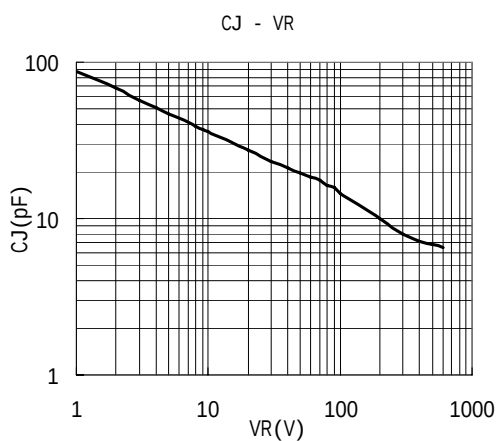
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal resistance, junction to case	$R_{\theta Jc}$	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

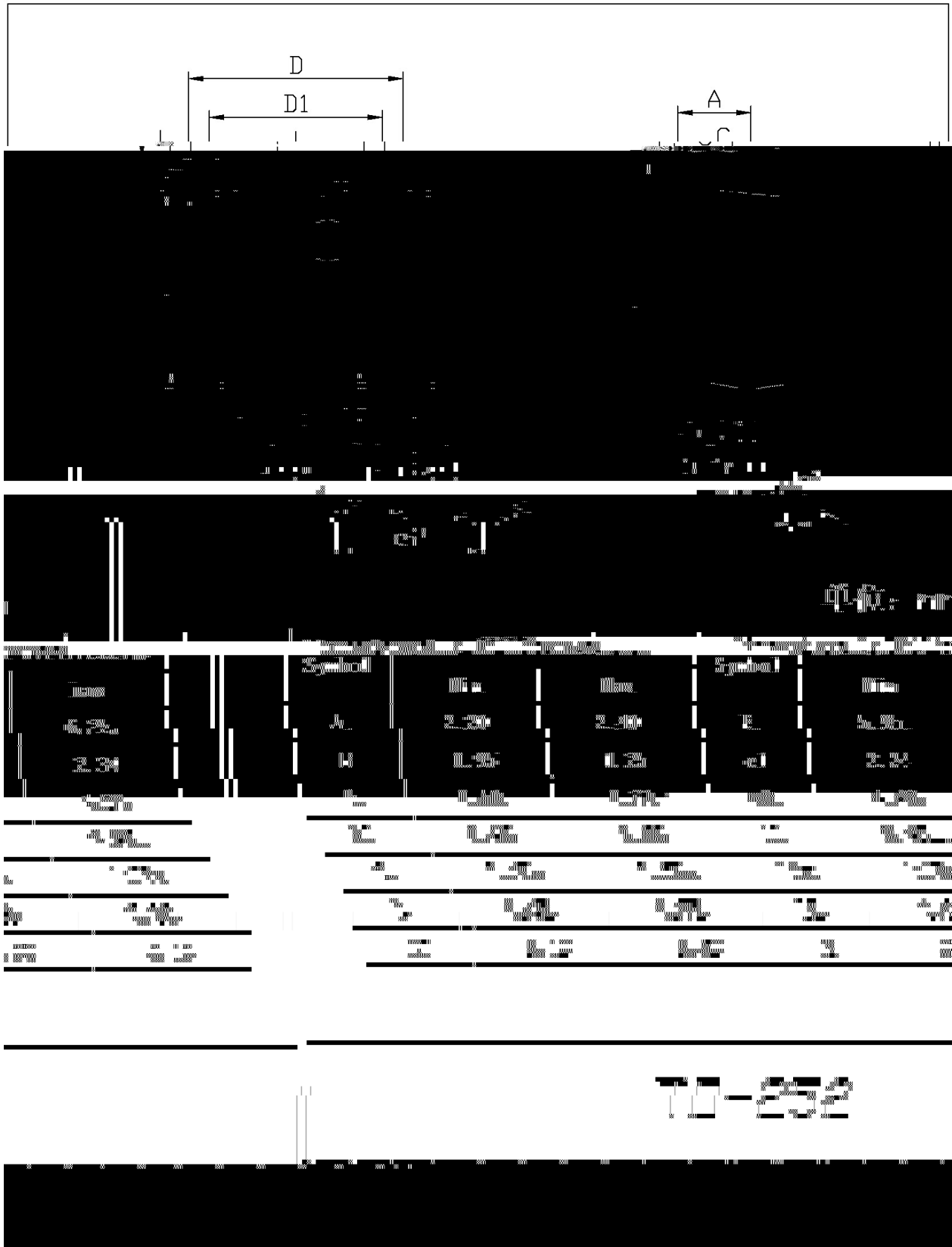
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	$I_R=100\mu A$	600			V
Forward Voltage	V_F	$I_F=8A$ $T_c=25$		1.4	1.7	V
		$I_F=16A$ $T_c=25$		1.7	2.1	V

I_F

/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



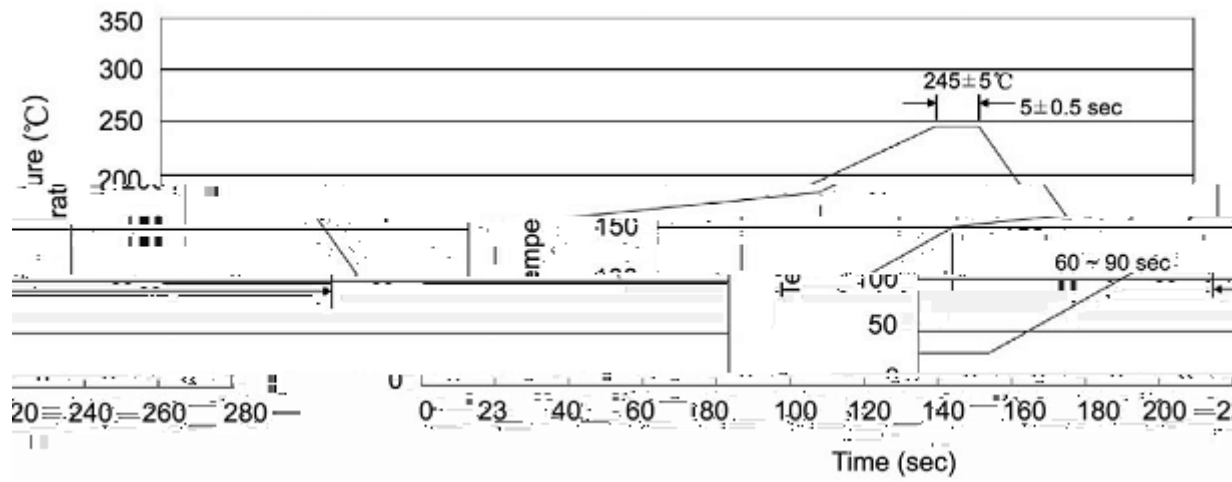
Note:

BR: Company Code

Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |